



DOCUMENT CHANGE REQUEST

DCR number	1394	Changes required for:	General	Originator:	Steve Jeffery
Date:	2020/12/03	Date sent:	2020/11/12	Organisation:	ESCC Executive
Status:	IMPLEMENTED				

Title: Transistors, Power, MOSFET, N-Channel, RAD-HARD, based on Type STRH100N10FSY3

Number: 5205/021 Issue: 8

Other documents affected:

Page:

15, 16

Paragraph:

2.12.2, Appendix A

Original wording:

IGSS1 Drift Value limit: +15nA
IGSS2 Drift Value limit: -15nA
IDSS Drift Value limit: +4uA
VGS(th) Drift Value limits: -50% / +5%
Characteristics are specified for "Total Gate Charge", "Gate-to-Source Charge" and "Gate-to-Drain Charge" (Qg, Qgs and Qgd)

Proposed wording:

IGSS1 Drift Value limit: +20nA
IGSS2 Drift Value limit: -20nA
IDSS Drift Value limit: -
VGS(th) Drift Value limits: -50% / +10%
Qg, Qgs and Qgd removed from the table and associated Agreed Deviation in Appendix A is deleted.

See attached MSWord file of 5205/021 Draft 9A, where all proposed changes are highlighted in yellow.

Justification:

Note: this DCR has been raised by the ESCC T.W. on behalf of the ESCC Qualified mfr STMicroelectronics.

For 5205/021 (STRH100N10), ST wish to align some of the Drift Value limits for Electrical Measurements for Total Dose Radiation Testing with those defined in ESCC 5205/026 because the N-Channel rad-hard power MOSFETs in both these specs are similar. (These proposed changes are considered by the T.W. to be technically acceptable.)

Attachments:

esc5205021iss9drafta_for_dcr_review.docx

Modifications:

N/A

Approval signature:

A handwritten signature in black ink, appearing to be "H. J. ...", is written in the signature field.

Date signed:

2020-12-03